

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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# 2SC5850

Silicon NPN Epitaxial

**RENESAS**

ADE-208-1479 (Z)

Rev.0  
Feb. 2002

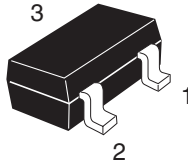
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## Features

- Low frequency amplifier

## Outline

CMPAK



1. Emitter
2. Base
3. Collector

## Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	50	V
Collector to emitter voltage	$V_{CEO}$	40	V
Emitter to base voltage	$V_{EBO}$	5	V
Collector current	$I_C$	100	mA
Emitter current	$I_E$	-100	mA
Collector power dissipation	$P_C^*$	150	mW
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to +125	°C

\*Value on the glass epoxy board (10 mm x 10 mm x 0.7 mm)

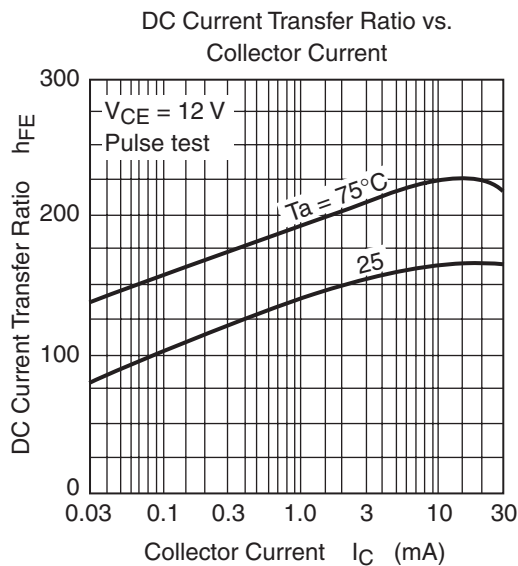
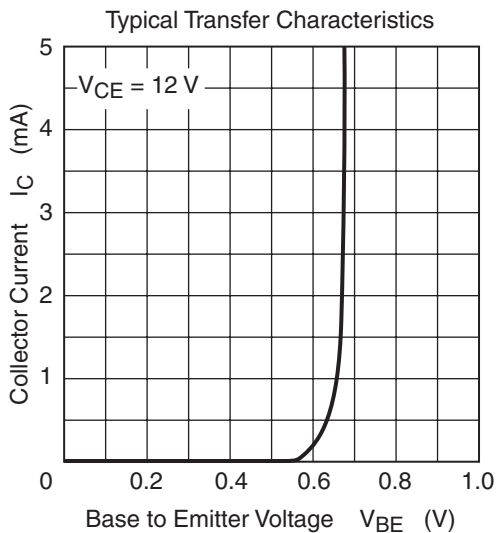
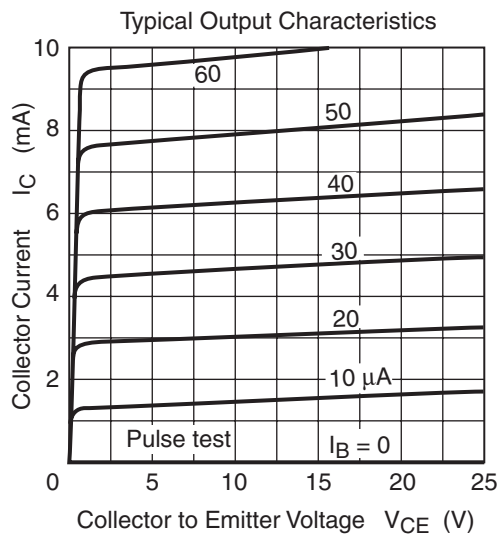
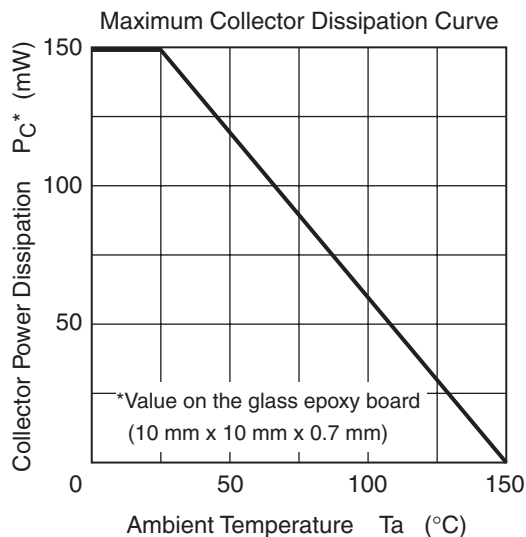
## Electrical Characteristics

(Ta = 25°C)

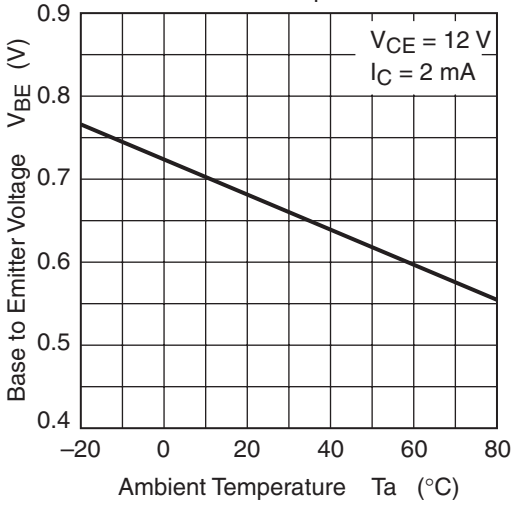
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	40	—	—	V	$I_C = 1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	0.5	$\mu A$	$V_{CE} = 30 \text{ V}, I_E = 0$
Emitter cutoff current	$I_{EBO}$	—	—	0.5	$\mu A$	$V_{EB} = 2 \text{ V}, I_C = 0$
DC current transfer ratio	$h_{FE}^{*1}$	100	—	500	—	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.2	V	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	0.75	V	$V_{CE} = 12 \text{ V}, I_C = 2 \text{ mA}$

Notes: 1. The 2SC5850 is grouped by  $h_{FE}$  as follows.

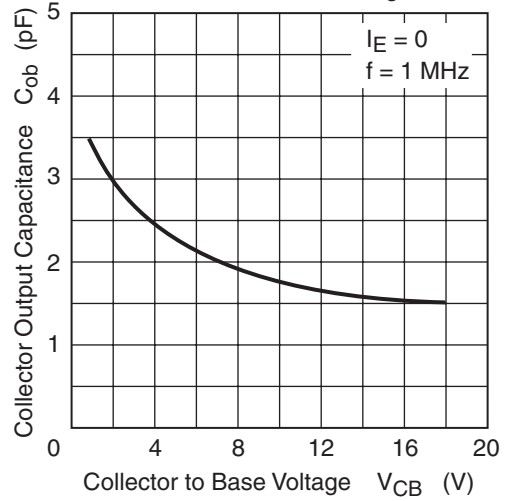
Grade	B	C	D
Mark	LB	LC	LD
$h_{FE}$	100 to 200	160 to 320	250 to 500



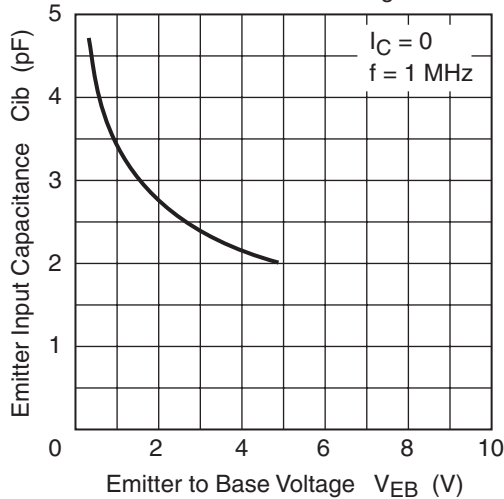
Base to Emitter Voltage vs. Ambient Temperature



Collector Output Capacitance vs. Collector to Base Voltage



Emitter Input Capacitance vs. Emitter to Base Voltage





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